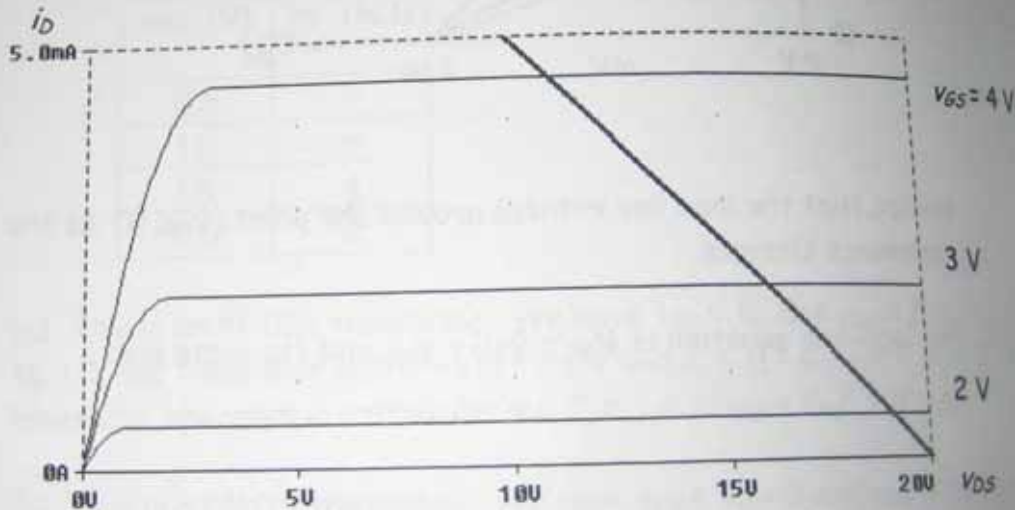


P12.20 (a) The  $1.7 \text{ M}\Omega$  and  $300 \text{ k}\Omega$  resistors act as a voltage divider that establishes a dc voltage  $V_{GSQ} = 3 \text{ V}$ . Then if the capacitor is treated as a short for the ac signal, we have

$$v_{GS}(t) = 3 + \sin(2000\pi t)$$

(b), (c), and (d)



P12.26\* For this circuit, we can write

$$V_{GSQ} = 15 - I_{DQ}R_S$$

Assuming operation in saturation, we have

$$I_{DQ} = K(V_{GSQ} - V_{t0})^2$$

using the first equation to substitute into the second equation, we have

$$I_{DQ} = K(15 - I_{DQ}R_S - V_{t0})^2 = 0.25(14 - 3I_{DQ})^2$$

where we have assumed that  $I_{DQ}$  is in mA. Rearranging and substituting values, we have

$$I_{DQ}^2 - 9.777I_{DQ} + 21.777 = 0$$

P12.31 We have  $V_G = V_{GSQ} = 10R_2/(R_1 + R_2) = 2.5 \text{ V}$ . Then we have  $I_{DQ} = K(V_{GSQ} - V_{t0})^2 = 0.5625 \text{ mA}$ .  $V_{DSQ} = V_{DD} - R_D I_{DQ} = 4.375 \text{ V}$ .

P12.39

$$g_m = \left. \frac{\partial i_D}{\partial v_{GS}} \right|_{Q\text{-point}} = 9v_{GS}^2 \Big|_{Q\text{-point}} = 9 \text{ mS}$$

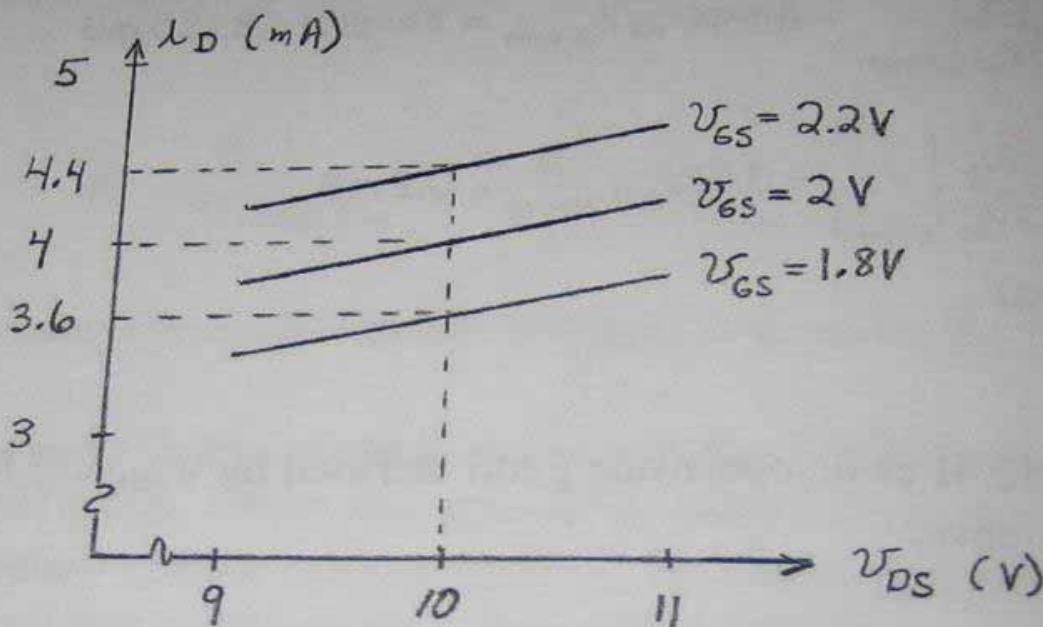
$$1/r_d = \left. \frac{\partial i_D}{\partial v_{DS}} \right|_{Q\text{-point}} = 0.1 \Big|_{Q\text{-point}} = 0.1 \text{ mS}$$

$$r_d = 10 \text{ k}\Omega$$

P12.42 We will sketch the characteristics for  $v_{GS}$  ranging a few tenths of a volt on either side of the  $Q$  point.  $g_m$  determines the spacing between the characteristic curves. For  $g_m = 2 \text{ mS}$ , the curves move upward by  $0.2 \text{ mA}$  for each  $0.1 \text{ V}$  increase in  $v_{GS}$ .

Also, we will sketch the characteristics for  $v_{DS}$  ranging a few volts on either side of the  $Q$  point.  $r_d$  determines the slope of the characteristic curves. For  $r_d = 5 \text{ k}\Omega$ , the curves slope upward by  $0.2 \text{ mA}$  for each  $1 \text{ V}$  increase in  $v_{DS}$ .

The sketch of the curves is:



$$\text{P12.45* (a)} \quad V_G = V_{DD} \frac{R_2}{R_1 + R_2} = 20 \frac{0.3}{1.7 + 0.3} = 3 \text{ V}$$

$$V_{GSQ} = V_G = 3 \text{ V}$$

$$K = \frac{1}{2} KP(W/L) = 2.5 \text{ mA/V}^2$$

$$I_{DQ} = K(V_{GSQ} - V_{to})^2 = 10 \text{ mA}$$

$$V_{DSQ} = V_{DD} - R_D I_{DSQ} = 10 \text{ V}$$

$$g_m = 2\sqrt{KI_{DQ}} = 0.01 \text{ S}$$

$$\text{(b)} \quad R'_L = \frac{1}{1/R_D + 1/R_L} = 500 \Omega$$

$$A_v = -g_m R'_L = -5$$

$$R_{in} = \frac{1}{1/R_1 + 1/R_2} = 255 \text{ k}\Omega$$

$$R_o = R_D = 1 \text{ k}\Omega$$

**P12.50** If we need a voltage-gain magnitude greater than unity, we choose a common-source amplifier. To attain lowest output impedance usually a source follower is better.

P12.51\* We have

$$K = \left(\frac{W}{L}\right) \frac{KP}{2} = 400 \mu\text{A}/\text{V}^2$$

Assuming operation in saturation, we have

$$I_{DQ} = K(V_{GSQ} - V_{to})^2$$

Solving for  $V_{GSQ}$  and evaluating we have

$$V_{GSQ} = V_{to} + \sqrt{I_{DQ}/K} = 3.236 \text{ V}$$

$$V_G = V_{DD} \frac{R_2}{R_1 + R_2} = 10 \text{ V}$$

$$V_G = V_{GSQ} + R_S I_{DQ}$$

Solving for  $R_S$  and substituting values we have

$$R_S = (V_G - V_{GSQ})/I_{DQ} = 3.382 \text{ k}\Omega$$

We have  $g_m = 2\sqrt{KI_{DQ}} = 1.789 \text{ mS}$

$$R'_L = \frac{1}{1/R_L + 1/R_S + 1/r_d} = 1.257 \text{ k}\Omega$$

$$A = \frac{v_o}{v_{in}} = \frac{g_m R'_L}{1 + g_m R'_L} = 0.6922$$

$$R_{in} = \frac{v_{in}}{i_{in}} = R_G = R_1 \parallel R_2 = 666.7 \text{ k}\Omega$$

$$R_o = \frac{1}{g_m + \frac{1}{R_s} + \frac{1}{r_d}} = 386.9 \Omega$$



P12.52 (a) We start by assuming that the MOSFET is operating in the saturation region, so we have

$$I_{DQ} = K(V_{GSQ} - V_{to})^2$$

Also, we have  $K = \frac{1}{2}KP(W/L) = 1.5 \text{ mA/V}^2$

For a dc Q-point analysis, the capacitors behave as open circuits. Writing a voltage equation from the gate through  $R_s$  and back to ground through the  $V_{SS}$  source, we obtain

$$V_{GSQ} + R_s I_{DQ} = V_{SS}$$

Substituting for  $I_{DQ}$  we have

$$V_{GSQ} + R_s K(V_{GSQ} - V_{to})^2 = V_{SS}$$

Then substituting numerical values, we have

$$V_{GSQ} + 4.5(V_{GSQ} - 1)^2 = 15$$

Solving, we obtain  $V_{GSQ} = 2.656 \text{ V}$  (The other root is extraneous.) Then we have

$$I_{DQ} = K(V_{GSQ} - V_{to})^2 = 4.114 \text{ mA}$$

$$V_{DSQ} = 30 - I_{DSQ}(R_s + R_D) = 5.316 \text{ V}$$

Since  $V_{DSQ}$  is higher than  $V_{GSQ} - V_{to}$  the assumption that the device operates in the saturation region is valid.

$$g_m = 2\sqrt{KI_{DQ}} = 4.968 \text{ mS}$$

(b) Using the results from Exercise 12.13, we have

$$R'_L = R_D \parallel R_L = 2.308 \text{ k}\Omega$$

$$A_v = v_o/v_{in} = R'_L g_m = 11.465$$

$$R_{in} = \frac{v_{in}}{i_{in}} = \frac{1}{g_m + 1/R_s} = 188.6 \Omega$$